

N (688396)

1 12.16 A 8.79 2003
 100% 2 6 3 CRH Mi cro
 1 3 8 2
 IDM
 IDM
MOSFET
 MOSFET IGBT 2019
 35%
 Marki t MOSFET IHS
 MOSFET IGBT
 IGBT 600V-6500V IGBT
 IGBT
Si C GaN
 Si C MOSFET IGBT
 SBD Yol e
 2017-2023 Si C 31%
 2023 15
 Si C GaN Yol e
 2022 GaN 4.5
 GaN

688396
 52 /
 ()
 ()
 () 237.14
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 SAC NO S1120519090003



Si C				650V	IDM GaN
Si C JBS	Si C MOSFET				
2019-2021			57.45		69.60
83.52	-8.39%	21.15%	20%		
	4.01	6.35	8.16		
			2021	PE	
40	100			MOSFET	

	2017A	2018A	2019E	2020E	2021E
()	5875.59	6270.80	5745.00	6960.00	8352.00
YoY	33.63%	6.73%	-8.38%	21.15%	20.00%
()	70.28	429.44	400.75	651.91	833.59
YoY	123.22%	511.02%	-6.68%	62.67%	27.87%
	17.62%	25.20%	23.50%	27.00%	28.00%
	0.06	0.37	0.34	0.56	0.71
ROE	1.83%	10.35%	4.38%	6.65%	7.84%
	0.00	0.00	0.00	0.00	0.00

Wind





9 2016-2019H1

10

11

12 MOS

13 2018 MOSFET %

14 Transistor/IGBT/MOSFET

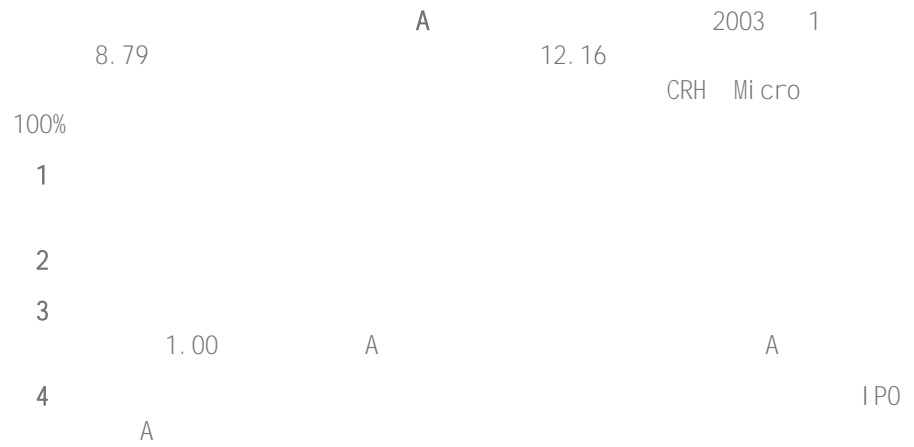
15 IGBT

16

17

1. IDM&

1.1. A



1



2 2004~2013



3 2014~2020





2	2018
	2018
1	21.7
2	18.5
3	17.1
4	8.1
5	7.7
6	7.2
7	6.9
8	6
9	5.4
10	4.9





4

MOSFET	MOS	MOS	MOS	MOS
	-100V-	1500V		
IGBT			600V-	1200V
SBD	SBD		SBD	
	200mA-		45V-	150V
FRD			200V-	6500V

5

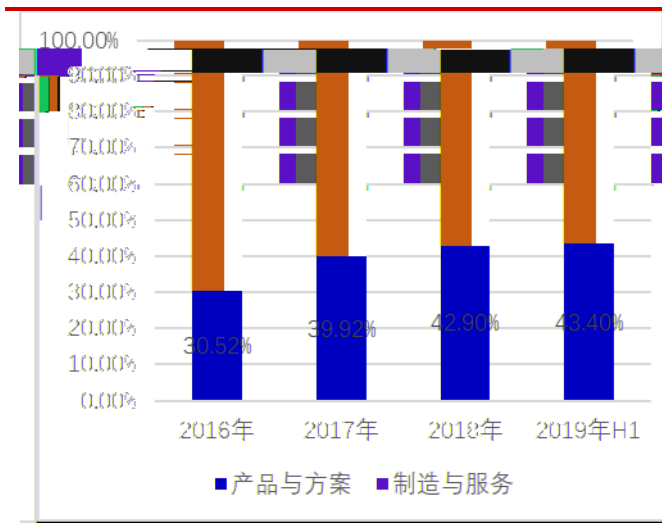
IC IC

AC-DC		AC-DC
LED	IC	LED
BMS	EMC/31D7C	



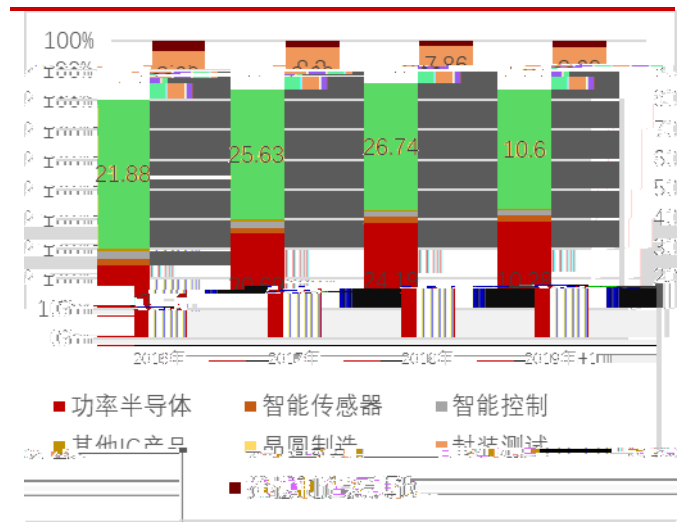
6 2016-2019H1

%



Wind

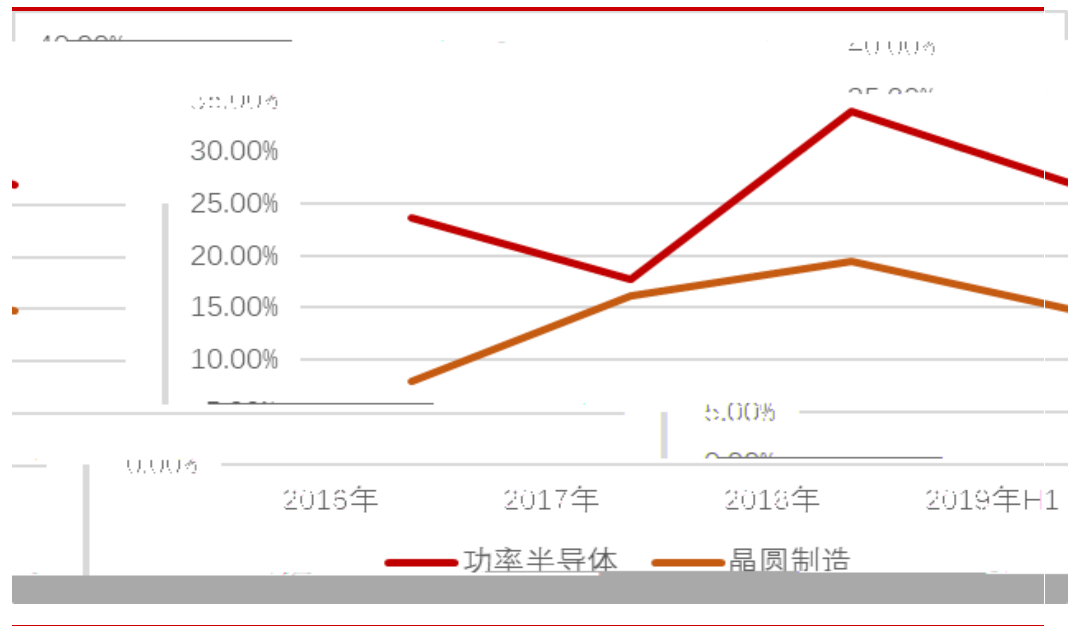
7 2016-2019H1



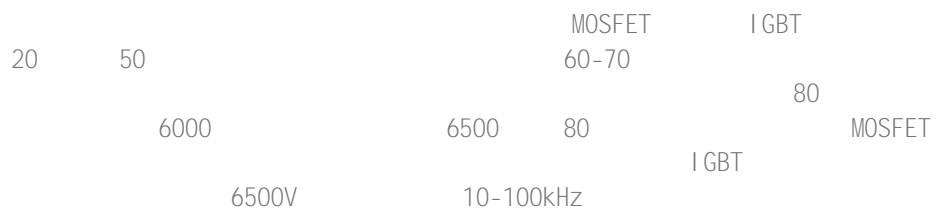
Wind

8

%



1.3.

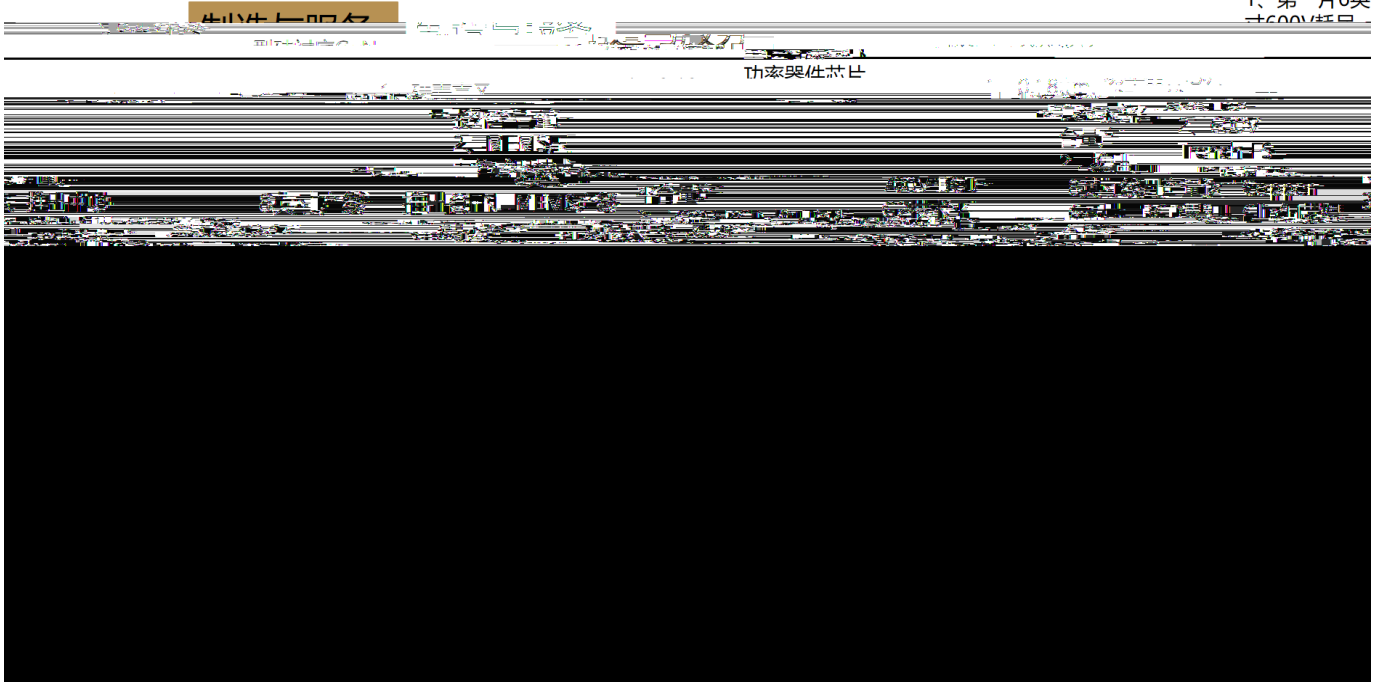


SBD

BCD

20

9 2008-2018



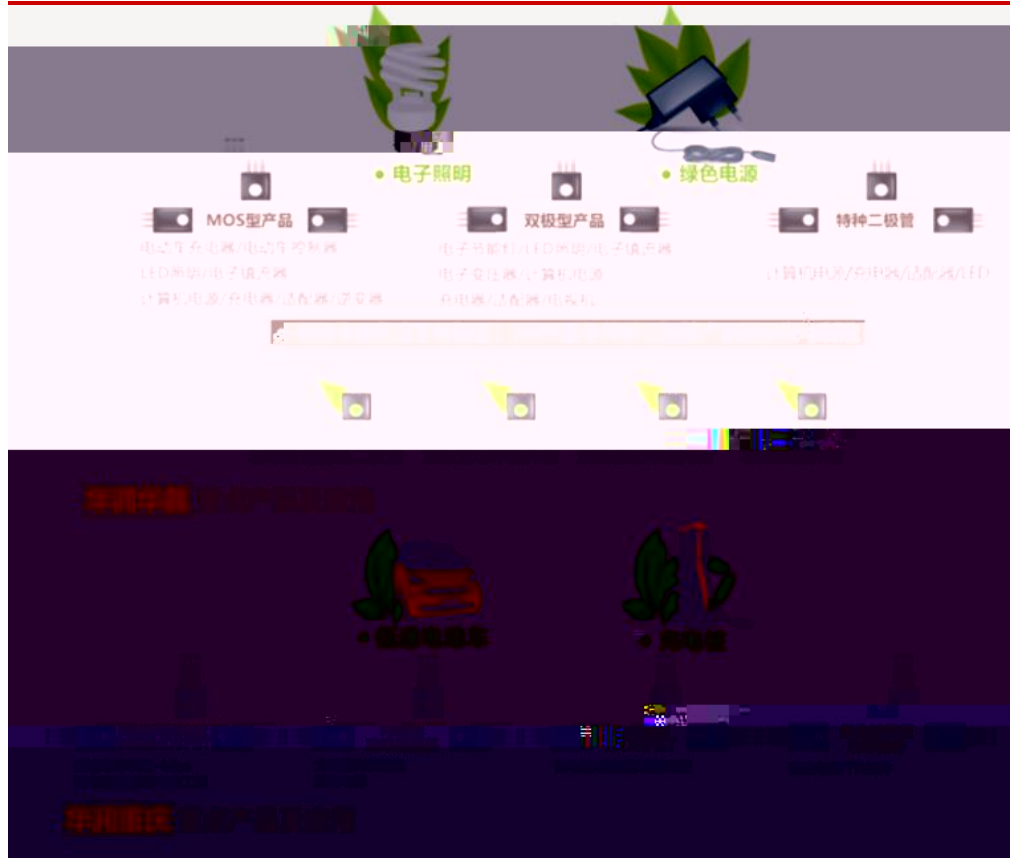
BCD

MEMS

IGBT SBD FRD
 Trench-FS
 8 Trench
 FRD

600V-6500V IGBT

SBD





90nm-0.13um

MCU

MCU

DSP FPGA



9 2016~2019H1

IGBT

IGBT MOSFET IGBT
 /

2. 2. MOSFET

IDM

-2018	IHS Markit	2018	MOSFET P8p	27.92	2016
		15.03%			



MOSFET

IDM

-100V 1500V
MOSFET

MOSFET

MOS VDMOS MOS

MOSFET

12 MOS

30V-900V	40V-900V	-60V-150V	-100V-1500V
MOS	MOS	MOS	MOS
MOS	MOS	MOS	MOS
MOS		MOS	MOS
MOS		P MOS	MOS
MOS			MOS
			P MOS

MOSFET
MOSFET

IDM

MOSFET

2018

MOSFET

MOSFET

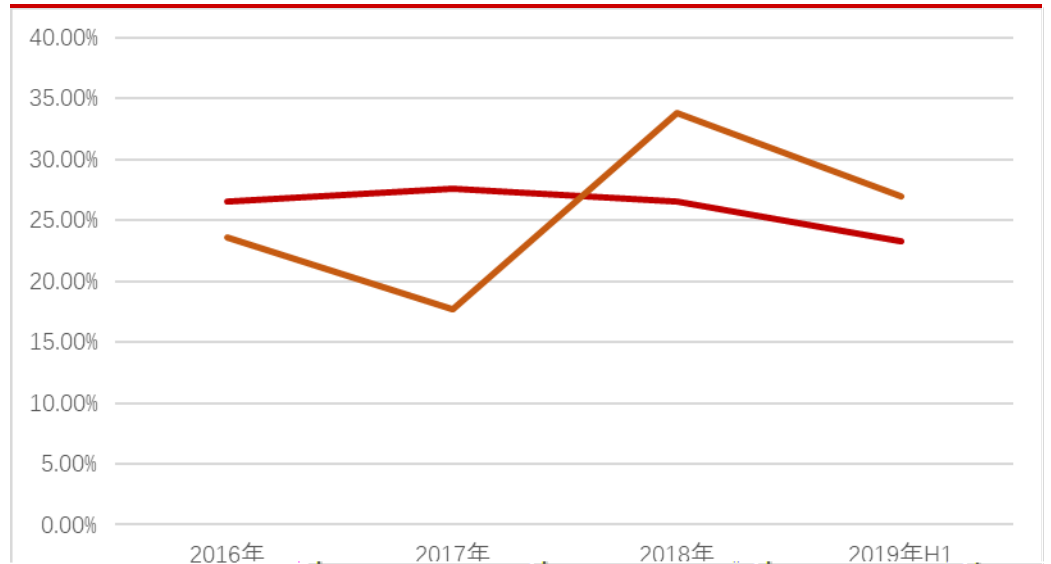
IHS Market

MOSFET

MOSFET
MOSFET

16 2016-2019H1

%



— 行业平均值 — 公司功率半导体



13 2018	MOSFET		%
	2018	MOS	
		52	28.40%
		31	16.90%
		16	8.70%
		12	6.60%
		12	6.60%
		9	4.90%
		51	27.90%
		183	100%

2.3. IGBT

IGBT Insulated Gate Bipolar Transistor
BJT MOSFET

MOSFET
BJT

IGBT 20 80
MOSFET GTR SCR GTO
BJT



1

2

3

(Si C)

3C-Si C
10

4H-Si C

6H-Si C

4H-Si C

3

2

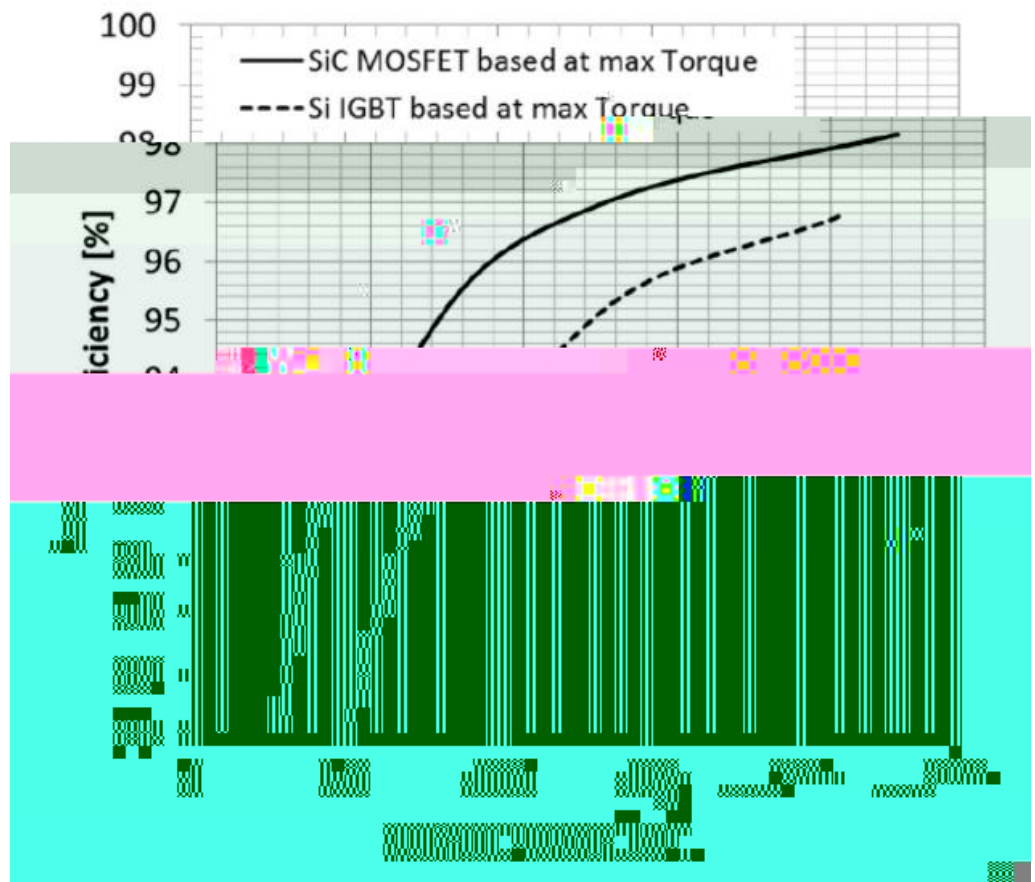
3

Si C

Si C

MOSFET IGBT SBD

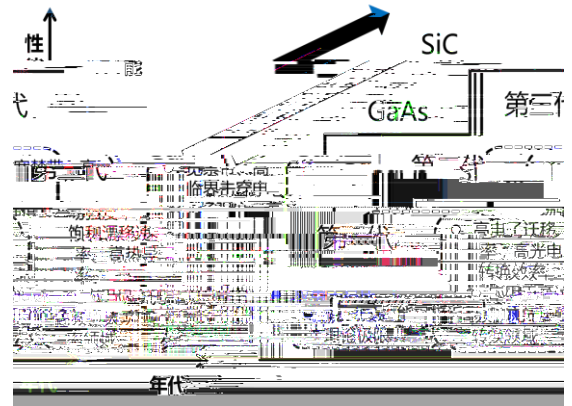
21 Si C MOSFET Si IGBT



22



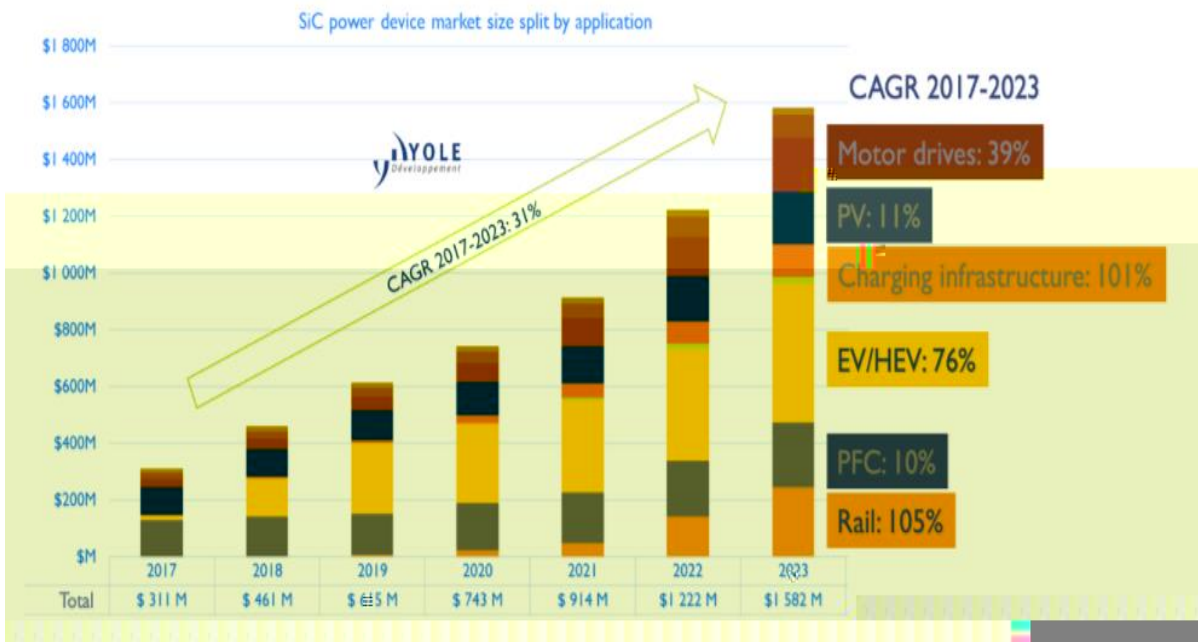
23



Google

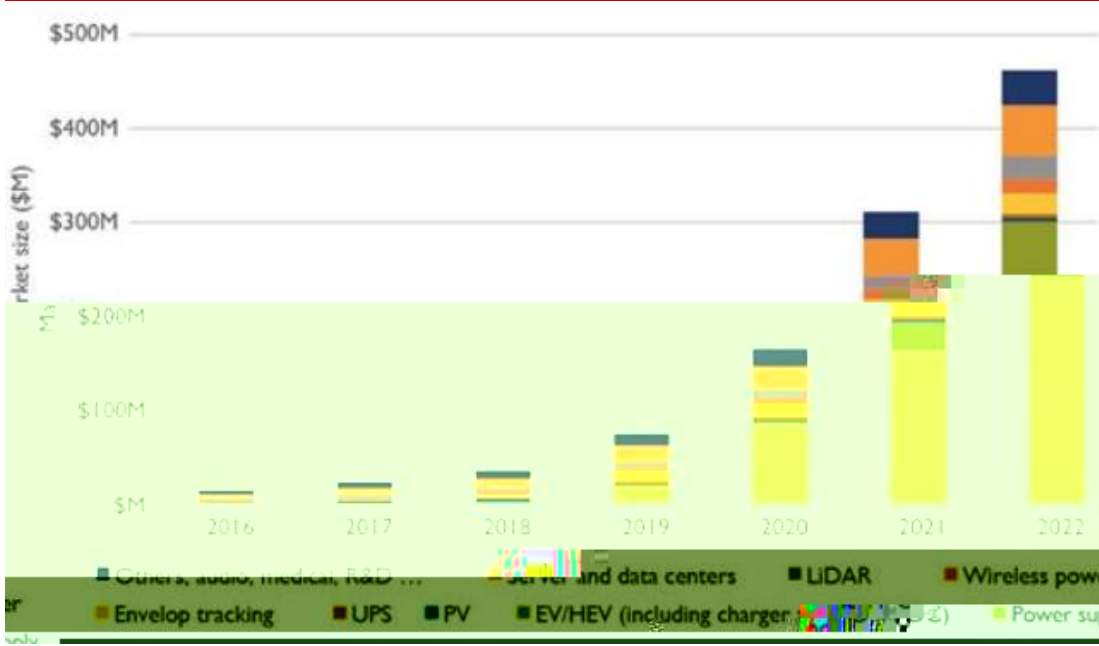
YoY	2023	2023	2017-2023	15	SiC	31%
	76%				CAGR	101%

24 2017~2023 SiC



YoY

25 GaN



Cool GaN

GaN

Si C

GaN

5G

YoI e

2022 GaN

Si C 4.5

3.

-2018	IHS Market	2018	MOSFET	27.92	2016
		15.03%			
	MOSFET		MOSFET		Type-C
	2019~2021		8		2019
			-8.39%	21.15%	20%
		2019			
			6	/8	5G
100.32%/102.32%		2018			23.5%
		2019~2021			27%
					28%
	2019~2021		57.45	69.60	83.52
-8.39%	21.15%	20%		4.01	6.35
8.16				2021	PE
	100		MOSFET		40

17

	2020	2021	PE(21)	PE(20)
300046.SZ	56.37	1.48	1.87	30.12
300373.SZ	145.32	3.04	3.88	37.45
300623.SZ	122.22	2.37	2.93	41.67
600460.SH	247.72	1.54	1.85	134.16
600745.SH	1,753.49	31.47	40.56	43.23
603290.SH	134.98	1.75	2.41	55.99

Wind

2020 2 26

4.

2.41



	2018A	2019E	2020E	2021E		2018A	2019E	2020E	2021E
	6270.80	5745.00	6960.00	8352.00		537.56	512.43	869.21	1111.46
Y(%)	6.73%	-8.38%	21.15%	20.00%		953.19	868.90	908.90	948.90
	4690.26	4394.93	5080.80	6013.44		-95.14	-39.31	-233.97	-140.00
